



**SOT-23 Plastic-Encapsulate MOSFETS**

**MK3403**

**P-Channel 30-V(D-S) MOSFET**

V(BR)DSS	RDS(on)MAX	ID
-30 V	115mΩ@-10V	-2.6A
	140mΩ@-4.5V	
	170mΩ@-2.5V	

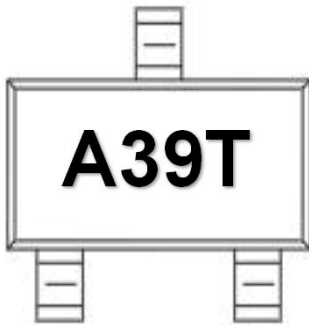
**FEATURE**

※ TrenchFET Power MOSFET

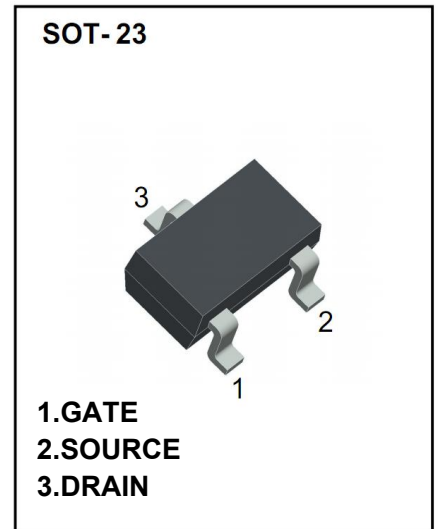
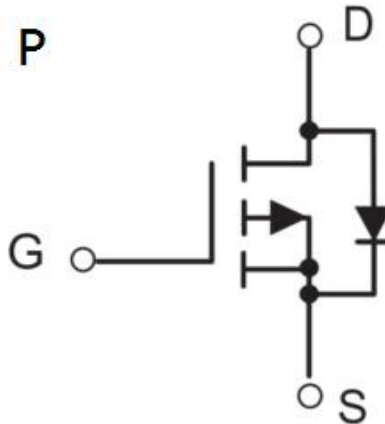
**General Description**

The MK3403 uses advanced trench technology to provide excellent RDS(ON) and low gate charge. This device is suitable for use as a load switch or in PWM applications. Standard Product MK3403 is Pb-free (meets ROHS & Sony 259 specifications).

**MARKING:**



**Equivalent Circuit**



**Maximum ratings ( Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-30	V
Gate-Source Voltage	VGS	±12	
Continuous Drain Current	ID	-2.6	A
Pulsed Diode Current	IDM	-20	
Continuous Source-Drain Current(Diode Conduction)	IS	-1	
Power Dissipation	PD	1.4	W
Thermal Resistance from Junction to Ambient (t≤10s)	RθJA	125	°C/W
Operating Junction	TJ	150	°C
Storage Temperature	TSTG	-55~+150	°C



**MOSFET ELECTRICAL CHARACTERISTICS**

**Static Electrical Characteristics (Ta = 25 °C Unless Otherwise Noted)**

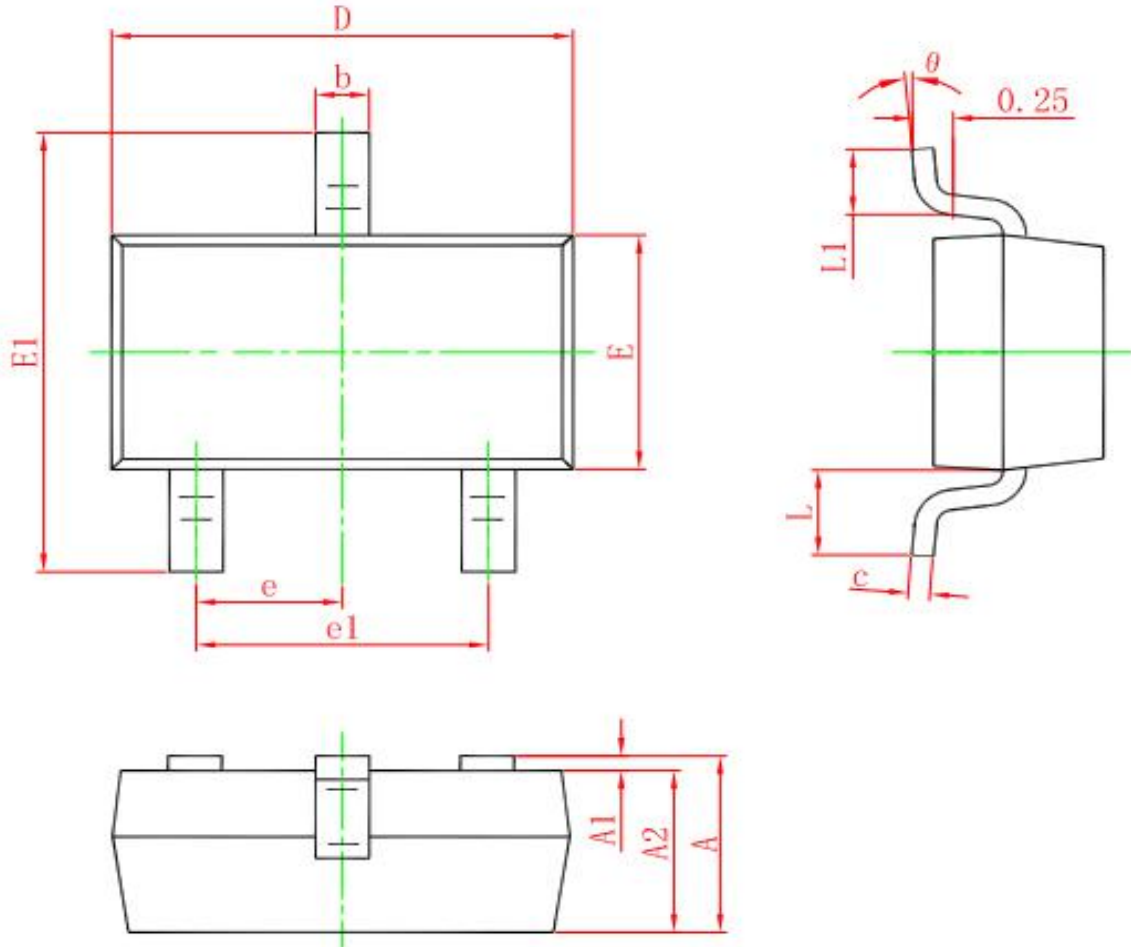
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = -250μA	-30			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = -250μA	-0.6		-1.1	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±12V			±100	nA
Zero gate voltage drain current	IDSS	VDS = -30V, VGS =0V			-1	μA
Drain-source on-state resistancea	RDS(on)	VGS = -10V, ID = -2.6A		88	115	mΩ
		VGS = -4.5V, ID = -2A		96	140	mΩ
		VGS = -2.5V, ID = -1A		107	170	mΩ
Forward transconductancea	gfs	VDS = -4.5V, ID = -2.5A		4.5		S
Diode forward voltage	VSD	IS=-1A,VGS=0V		-0.8	-1.3	V
<b>Dynamic</b>						
Input capacitance	Ciss	VDS = -15V, VGS =0V, f=1MHz		409	500	pF
Output capacitance	Coss			55		pF
Reverse transfer capacitanceb	Crss			42		pF
Total gate charge	Qg	VDS = -15V, VGS = -4.5V, ID =-2.5A		4.4	5.3	nC
Gate-source charge	Qgs			0.8		nC
Gate-drain charge	Qgd			1.32		nC
Gate resistance	Rg	f=1MHz		12		Ω
<b>Switchingb</b>						
Turn-on delay time	td(on)	VDS= -15V RL=6Ω, ID ≈ -1.5A, VGEN=- 4.5V,Rg=3Ω		5.3	8	ns
Rise time	tr			4.4	9	ns
Turn-off delay time	td(off)			31.5	45	ns
Fall time	tf			8	16	ns
<b>Drain-source body diode characteristics</b>						
Continuous Source-Drain Diode Current	IS	Tc=25°C			-2.6	A
Pulsed Diode forward Curren	ISM				-12	A

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 10 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.



SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
theta	0°	8°	0°	8°